



N-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS}(V)$ $R_{DS(on)}(\Omega)$		Q _g (Typ.)		
20	0.091 at V _{GS} = 4.5 V	1.3 ^a	3.5		
	0.124 at V _{GS} = 2.5 V	1.1	3.5		

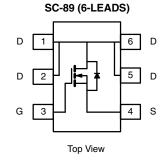
FEATURES

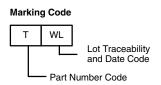
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R_q and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

· Load Switch for Portable Devices





Ordering Information: Si1058X-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	S (T _A = 25 °C, un	less otherwi	se noted)		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	20	V	
Gate-Source Voltage		V _{GS}	V _{GS} ± 12		
Continuous Dunin Courset /T. 150 °CV8	T _A = 25 °C	L	1.3 ^{b, c}		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C	- I _D	1.03 ^{b, c}	Α Α	
Pulsed Drain Current		I _{DM}	6	^	
Avalanche Current L = 0.1 mH		I _{AS}	7		
Repetitive Avalanche Energy	L = 0.1 IIII	E _{AS}	2.45	mJ	
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	0.2 ^{b, c}	A	
Mariana Parana Dissipational	T _A = 25 °C	P _D	0.236 ^{b, c}	w	
Maximum Power Dissipation ^a	T _A = 70 °C] 'D	0.151 ^{b, c}	VV	
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Typical	Maximum	Unit		
Manifestor Londing to Applicate d	t ≤ 5 s	R _{thJA}	440	530	°C/W	
Maximum Junction-to-Ambient ^{b, d}	Steady State	' ¹thJA	540	650	C/VV	

Notes:

- a. Based on T_C = 25 °C.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s
- d. Maximum under steady state conditions is 650 °C/W.

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Parameter	Symbol	Min.	Тур.	Max.	Unit		
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	20			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		18.9		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	η ΙΔ = 250 μΑ		- 3.6			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.7		1.55	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA	
Zone Oote Weltere Due in Oromant	1	V _{DS} = 20 V, V _{GS} = 0 V			1	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V, T _J = 85 °C			10	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = \geq 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	6			Α	
Durate Occurred On Ot 1 Day 1 1 2	D	V _{GS} = 4.5 V, I _D = 1.3 A		0.076	0.091		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 2.5 V, I _D = 1.1 A		0.103	0.124	Ω	
Forward Transconductance	9 _{fs}	V _{DS} = 10 V, I _D = 1.3 A		5.5		S	
Dynamic ^b			•			•	
Input Capacitance	C _{iss}			380			
Output Capacitance	C _{oss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		75		pF	
Reverse Transfer Capacitance	C _{rss}			45			
Total Cata Charge	0	Q_g $V_{DS} = 10 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 1.3 \text{ A}$		3.9	5.9	nC	
Total Gate Charge	Q_{g}			3.51	5.3		
Gate-Source Charge	Q _{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 1.3 \text{ A}$		0.82			
Gate-Drain Charge	Q_{gd}			0.61			
Gate Resistance	R _g	f = 1 MHz		4.3	5.6	Ω	
Turn-On Delay Time	t _{d(on)}			8	12		
Rise Time	t _r	$V_{DD} = 10 \text{ V}, R_{L} = 15 \Omega$		20	30	ns	
Turn-Off DelayTime	t _{d(off)}	$I_D \cong 1.0 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		13	18		
Fall Time	t _f			6	9	1	
Drain-Source Body Diode Characterist	tics						
Pulse Diode Forward Current ^a	I _{SM}				6		
Body Diode Voltage	V _{SD}	I _S = 1.0 A		0.8	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			10.4	16	nC	
Body Diode Reverse Recovery Charge	Q _{rr}	Q _{rr}		3.7	5.7		
Reverse Recovery Fall Time	t _a	$I_F = 1.0 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$		6.5		ns	
Reverse Recovery Rise Time	t _b			3.9		1	

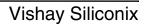
Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

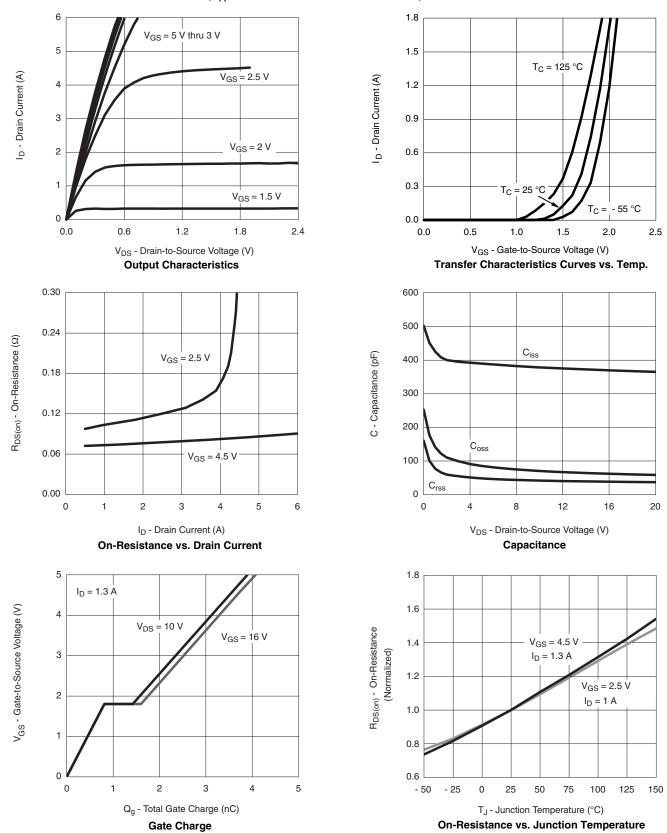
b. Guaranteed by design, not subject to production testing.







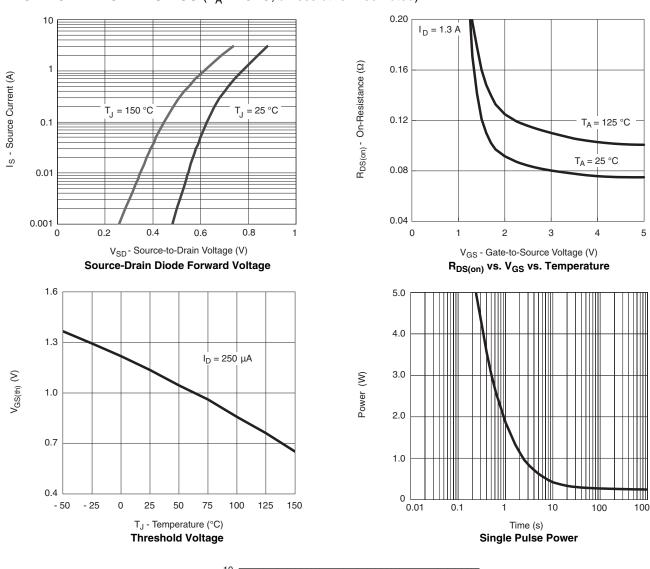
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)

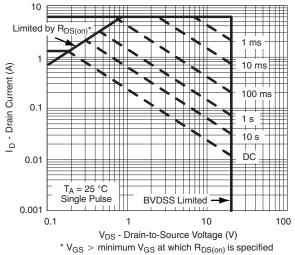


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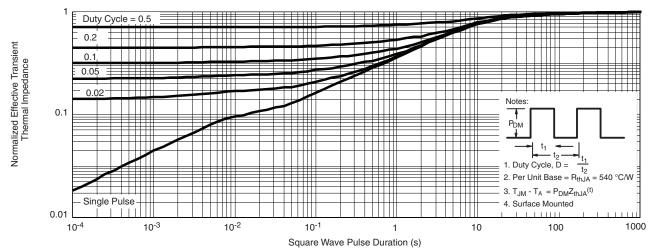








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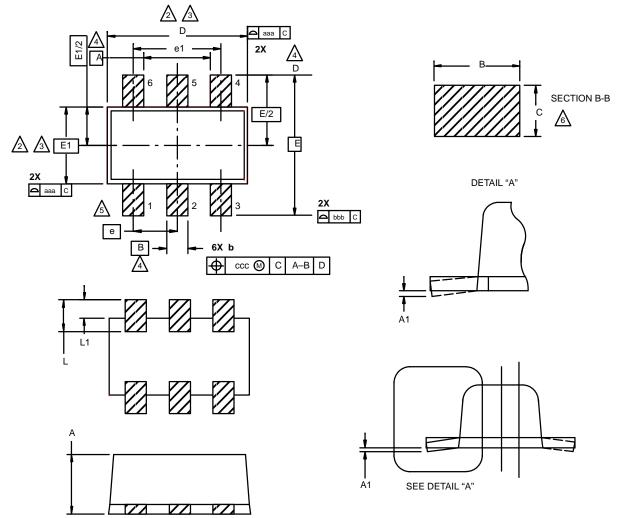


Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?73894.



SC89: 6- LEADS (SOT-563F)



NOTES:

1. Dimensions in millimeters.



Dimension D does not include mold flash, protrusions or gate burrs. Mold flush, protrusions or gate burrs shall not exceed 0.15 mm per dimension E1 does not include interlead flash or protrusion, interlead flash or protrusion shall not exceed 0.15 mm per side.



Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, the bar burrs, gate burrs and interlead flash, but including any mismatch between the top and the bottom of the plastic body.



Datums A, B and D to be determined 0.10 mm from the lead tip.



Terminal numbers are shown for reference only.



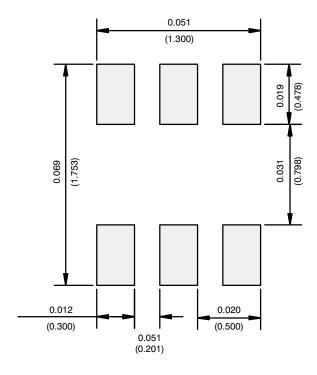
These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

	MILLIM	ILLIMETERS		Tolerances Of Form And				
Dim	Min	Max	Note	Symbol	Position			
Α	0.56	0.60		aaa	0.10			
A1	0.00	0.10		bbb	0.10			
b	0.15	0.30		ccc	0.10			
С	0.10	0.18						
D	1.50	1.70	2, 3					
E	1.55	1.70						
E1	1.20 BSC		2, 3					
е	0.50 BSC							
e1	1.00 BSC							
L	0.35 BSC							
L1	0.20 BSC							

DWG: 5880



RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

APPLICATION NOTE





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